

Customer No.: 31561
Docket No.:10/709,469
Application No.: 12129-US-PA

IN THE CLAIMS

Claim 1. (currently amended) A method of fabricating a flash memory cell, comprising the steps of:

- providing a substrate;
- forming a patterned mask layer over the substrate;
- etching the substrate using the patterned mask layer as an etching mask to form a trench in the substrate;
- forming a first dielectric layer over the substrate;
- forming a first gate and a second gate beside ~~the~~ respective sidewalls of the trench, wherein the first gate and the second gate are at a distance from each other and expose a portion of the first dielectric layer at ~~the~~ bottom of the trench;
- forming a first source/drain region in the substrate at the bottom of the trench;
- forming a second dielectric layer over the substrate;
- forming a passivation layer over the second dielectric layer;
- removing a portion of the passivation layer, the second dielectric layer and the first dielectric layer to expose ~~the~~ substrate surface at the bottom of the trench;
- forming a third gate that completely fills the trench;
- removing the patterned mask layer;
- forming a third dielectric layer over the substrate;
- forming a fourth gate and a fifth gate beside ~~the~~ respective sidewalls of the first gate and the second gate; and

Customer No.: 31561
Docket No.: 10/709,469
Application No.: 12129-US-PA

forming a second source/drain region in the substrate on one side of the fourth gate and the fifth gate.

Claim 2. (currently amended) The method of claim 1, wherein a material constituting the passivation layer comprises a semiconductor material or a conductive material.

Claim 3. (original) The method of claim 1, wherein a material constituting the passivation layer comprises undoped polysilicon.

Claim 4. (original) The method of claim 3, wherein the step of forming the passivation layer comprises performing a chemical vapor deposition process.

Claim 5. (original) The method of claim 3, wherein the passivation layer has a thickness of about 100Å.

Claim 6. (original) The method of claims 1, wherein a material constituting the first gate, the second gate, the third gate, the fourth gate and the fifth gate comprises undoped polysilicon.

Claim 7. (original) The method of claim 1, wherein the first gate and the second gate are floating gates, the third gate is a control gate, and the fourth gate and the fifth gate are select gates.

Claim 8. (original) The method of claim 1, wherein each of the fourth gate and the fifth gate comprises a doped polysilicon layer and a metal silicide layer.

Claim 9. (currently amended) The method of claim 1, wherein the first dielectric layer is a tunneling oxide layer and the second dielectric layer and the third dielectric layer

Customer No.: 31561
Docket No.: 10/709,469
Application No.: 12129-US-PA

are both inter-gate dielectric layers.

Claim 10. (currently amended) The method of claim 1, wherein the step of forming the first gate and the second gate on ~~the~~ respective sidewalls of the trench comprises:

depositing a conductive material into the trench to form a conductive layer;

performing an etching back operation so that a top section of the conductive layer is at a level lower than a surface of the patterned mask layer;

forming spacers on the sidewalls of the trench so that a portion of the conductive layer is covered; and

removing a portion of the conductive layer using the spacers and the patterned mask layer as an etching mask to form the first gate and the second gate beside the respective sidewalls of the trench.

Claim 11. (currently amended) The method of claim 1, wherein the step of forming the first gate and the second gate on ~~the~~ respective sidewalls of the trench comprises:

depositing a conductive material into the trench to form a conductive layer;

removing the conductive layer over ~~an~~ the upper surface of the patterned mask layer; and

patterning the conductive layer to form a first gate and a second gate beside the respective sidewalls of the trench.

Claim 12. (currently amended) The method of claim 1, further comprising a step

Customer No.: 31561
Docket No.: 10/709,469
Application No.: 12129-US-PA

of forming a liner layer over the substrate before the step of forming the patterned mask layer over the substrate, and a step of removing the liner layer during the step of removing the patterned mask layer.

Claim 13. (currently amended) The method of claim 12, wherein a material constituting the liner layer comprises silicon oxide and a material constituting the patterned mask layer comprises silicon nitride.

Claim 14. (original) The method of claim 1, further comprising a step of forming a fourth dielectric layer over the substrate before the step of forming the patterned mask layer over the substrate.

Claim 15. (currently amended) A method of fabricating a flash memory cell, comprising the steps of:

providing a substrate, having a liner layer and a mask layer formed thereon, wherein an opening is formed in the liner layer and the mask layer and a trench is formed in the substrate below the opening;

forming a tunneling oxide layer on a surface of the trench;

depositing a conductive material into the trench to form a conductive layer;

performing a etching back process so that a top section of the conductive layer is at a level higher than an upper surface of the liner layer but lower than an upper surface of the mask layer;

forming a pair of spacers on ~~the~~ the respective sidewalls of the trench so that a portion of the conductive layer is covered;

Customer No.: 31561
Docket No.:10/709,469
Application No.: 12129-US-PA

removing a portion of the conductive layer using the spacers and the mask layer as an etching mask to form a first floating gate and a second floating gate on the respective sidewalls of the trench;

forming a first source/drain region in the substrate at a bottom of the trench;

forming a first inter-gate dielectric layer on the substrate and over the surface of the trench;

forming a passivation layer over the first inter-gate dielectric layer;

removing portions of the passivation layer, the first inter-gate dielectric layer and the tunneling oxide layer until a portion of the substrate at the bottom of the trench is exposed;

forming a control gate that completely fills the trench, wherein a top section of the control gate is at a level higher than a top section of both the first floating gate and the second floating gate;

removing the liner layer and the mask layer;

forming a second inter-gate dielectric layer over the substrate;

forming a first select gate and a second select gate beside ~~the~~ respective sidewalls of the spacers, the first floating gate and the second floating gate; and

forming a second source/drain region in the substrate on one side of the first select gate and the second select gate.

Claim 16. (original) The method of claim 15, wherein a material constituting the passivation layer comprises a semiconductor material or a conductive material.

Customer No.: 31561
Docket No.:10/709,469
Application No.: 12129-US-PA

Claim 17. (original) The method of claim 15, wherein a material constituting the passivation layer comprises undoped polysilicon.

Claim 18. (original) The method of claim 17, wherein the step of forming the passivation layer comprises performing a chemical vapor deposition process.

Claim 19. (original) The method of claim 17, wherein a material constituting the conductive layer and the control gate comprises doped polysilicon.

Claim 20. (original) The method of claim 15, wherein the first inter-gate dielectric layer is a composite stack structure comprising a silicon oxide layer, a silicon nitride layer and another silicon oxide layer.

Claim 21. (original) The method of claim 15, wherein a material constituting the second inter-gate dielectric layer comprises a silicon oxide.

Claim 22. (original) The method of claim 15, wherein each of the first select gate and the second select gate comprise a doped polysilicon layer and a metal silicide layer.

Claim 23. (original) The method of claim 15, wherein a material constituting the liner layer comprises silicon oxide and a material constituting the mask layer comprises silicon nitride.

**This Page is Inserted by IFW Indexing and Scanning
Operations and is not part of the Official Record**

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images include but are not limited to the items checked:

- ☐ BLACK BORDERS
- ☐ IMAGE CUT OFF AT TOP, BOTTOM OR SIDES
- ☐ FADED TEXT OR DRAWING
- ☐ BLURRED OR ILLEGIBLE TEXT OR DRAWING
- ☐ SKEWED/SLANTED IMAGES
- ☐ COLOR OR BLACK AND WHITE PHOTOGRAPHS
- ☐ GRAY SCALE DOCUMENTS
- ☒ LINES OR MARKS ON ORIGINAL DOCUMENT
- ☐ REFERENCE(S) OR EXHIBIT(S) SUBMITTED ARE POOR QUALITY
- ☐ OTHER: _____

IMAGES ARE BEST AVAILABLE COPY.

As rescanning these documents will not correct the image problems checked, please do not report these problems to the IFW Image Problem Mailbox.